L	Hits	Search Text	DB	Time stamp
Number 1	3727	damascene	USPAT	2003/11/20
2	1009	damascene and barrier and electrode	USPAT	15:03 2003/11/20 15:33
3	781	(damascene and barrier and electrode) and (polishing or cmp or polished or planarize or planarizing) and (copper or	USPAT	2003/11/20
4	582	cu) (damascene and barrier and electrode) and ((polishing or cmp or polished or planarize or planarizing) same (copper or	USPAT	2003/11/20 09:50
5	193	cu)) ((damascene and barrier and electrode) and ((polishing or cmp or polished or planarize or planarizing) same (copper or	USPAT	2003/11/20
6	169	cu))) and capacitor (((damascene and barrier and electrode) and ((polishing or cmp or polished or planarize or planarizing) same (copper or	USPAT	2003/11/20 09:50
7	1968	cu))) and capacitor) and @ay<=2001 damascene and barrier and (copper or Cu) and (polishing or polished or cmp or	USPAT	2003/11/20 12:12
8	1775	planarize or planarizing or planarized) (damascene and barrier and (copper or Cu) and (polishing or polished or cmp or planarize or planarizing or planarized))	USPAT	2003/11/20 12:00
9	1160	not (((damascene and barrier and electrode) and ((polishing or cmp or polished or planarize or planarizing) same (copper or cu))) and capacitor) ((damascene and barrier and (copper or Cu) and (polishing or polished or cmp or planarize or planarizing or planarized)) not (((damascene and barrier and electrode) and ((polishing or cmp or polished or planarize or planarizing) same (copper or cu))) and capacitor)) and	USPAT	2003/11/20 12:01
10	858	via and trench (((damascene and barrier and (copper or Cu) and (polishing or polished or cmp or planarize or planarizing or planarized)) not (((damascene and barrier and electrode) and ((polishing or cmp or polished or planarize or planarizing) same (copper or cu))) and capacitor)) and	USPAT	2003/11/20 12:01
11	141	via and trench) and (dual adj damascene) ((((damascene and barrier and (copper or Cu) and (polishing or polished or cmp or planarize or planarizing or planarized)) not (((damascene and barrier and electrode) and ((polishing or cmp or	USPAT	2003/11/20 12:02
12	132	Cu) and (polishing or polished or cmp or planarize or planarizing or planarized)) not (((damascene and barrier and electrode) and ((polishing or cmp or polished or planarize or planarizing) same (copper or cu))) and capacitor)) and via and trench) and (dual adj damascene)) and (capacitor or capacitive)) and	USPAT	2003/11/20 14:23
13	5	@ay<=2001  ("5539231"   "5702981"   "5801094"    "5891799"   "5933761").PN	USPAT	2003/11/20 12:09

14	846	damascene and (liner or conformal) and (copper or Cu) and (polishing or polished or cmp or planarize or planarizing or	USPAT	2003/11/20 12:13
15	741	planarized) (damascene and (liner or conformal) and (copper or Cu) and (polishing or polished or cmp or planarize or planarizing or planarized)) and ((dual adj damascene) or (trench and via))	USPAT	2003/11/20 12:18
16	178	((damascene and (liner or conformal) and (copper or Cu) and (polishing or polished or cmp or planarize or planarizing or planarized)) and ((dual adj damascene) or	USPAT	2003/11/20 12:14
17	139	(trench and via))) and capacitor (((damascene and (liner or conformal) and (copper or Cu) and (polishing or polished or cmp or planarize or planarizing or planarized)) and ((dual adj damascene) or (trench and via))) and capacitor) not (((((damascene and barrier and (copper or Cu) and (polishing or polished or cmp or planarize or planarizing or planarized)) not (((damascene and barrier and electrode) and ((polishing or cmp or polished or planarize or planarizing) same (copper or cu))) and capacitor)) and via and trench) and (dual adj damascene)) and (capacitor or capacitive)) and @ay<=2001)	USPAT	2003/11/20 12:14
18	121	((((damascene and (liner or conformal) and (copper or Cu) and (polishing or polished or cmp or planarize or planarizing or planarized)) and ((dual adj damascene) or (trench and via)) and capacitor) not (((((damascene and barrier and (copper or Cu) and (polishing or polished or cmp or planarize or planarizing or planarized)) not (((damascene and barrier and electrode) and ((polishing or cmp or polished or planarize or planarizing) same (copper or cu))) and capacitor)) and via and trench) and (dual adj damascene)) and (capacitor or capacitive)) and @ay<=2001)) and @ay<=2001	USPAT	2003/11/20 12:14
19	59	· •	USPAT	2003/11/20 12:14

33	380	(((((damascene or (via and trench)) and (barrier or liner or conformal)) and	US-PGPUB	2003/11/20 14:40
		(polish or polishing or cmp or planarize		
		or planarizing)) and (copper or Cu)) and (mask or photo\$1resist)) and capacitor		
34	213	((((((damascene or (via and trench)) and	US-PGPUB	2003/11/20
<b>J</b> 1		(barrier or liner or conformal)) and		14:40
		(polish or polishing or cmp or planarize		
		or planarizing)) and (copper or Cu)) and		
		(mask or photo\$lresist)) and capacitor)		
35	650	and @ay<=2001 ((((damascene or (via and trench)) and	US-PGPUB	2003/11/20
33	050	(barrier or liner or conformal)) and	00 10102	14:44
		(polish or polishing or cmp or planarize		
		or planarizing)) and (copper or Cu)) and		
		((mask or photo\$lresist) with (trench or		
36	111	<pre>via)) ((((((damascene or (via and trench)) and</pre>	US-PGPUB	2003/11/20
36	111	(barrier or liner or conformal)) and	OD-FGFOD	14:52
		(polish or polishing or cmp or planarize		
		or planarizing)) and (copper or Cu)) and		
		(mask or photo\$1resist)) and capacitor)		
		and @ay<=2001) and ((mask or photo\$1resist) with (trench or via))		
37.	1	6329324.pn.	USPAT	2003/11/20
37.	1	00830871p		14:53
38	1	6329234.pn.	USPAT	2003/11/20
				15:14
39	14	("5194932"   "5208726"   "5293510"	USPAT	2003/11/20
		"5406447"   "5675184"   "5726083"     "5879985"   "5932906"   "5946569"		14.54
		"5998276"   "6146941"   "6184076"		
		"6258653"   "6259128").PN.		
42	15	("4481283"   "4959705"   "5065273"	USPAT	2003/11/20
		"5262354"   "5322812"   "5396094"		14:56
	ļ	"5406447"   "5459100"   "5479316"     "5502000"   "5576240"   "5602053"		
		"5858833"   "5858834"   "5861676").PN.		
43	2671	((dual adj damascene) or (trench and	USPAT	2003/11/20
	İ	via)) and ((barrier or liner or		15:05
		conformal) with (remove\$1 or removing or etch or etching or etched))		
44	886	(((dual adj damascene) or (trench and	USPAT	2003/11/20
1.7		via)) and ((barrier or liner or		15:05
		conformal) with (remove\$1 or removing or		
	}	etch or etching or etched))) and		
45	460	capacitor ((((dual adj damascene) or (trench and	USPAT	2003/11/20
45	460	(((dual ad) damasceme) or (cremen and   via)) and ((barrier or liner or	OSFAI	15:05
		conformal) with (remove\$1 or removing or		
		etch or etching or etched))) and	ĺ	
		capacitor) and (copper or Cu)		2002/11/02
46	245	(((((dual adj damascene) or (trench and	USPAT	2003/11/20 15:06
		via)) and ((barrier or liner or conformal) with (remove\$1 or removing or		13.00
		etch or etching or etched))) and		
		capacitor) and (copper or Cu)) and ((mask		
		or photo\$1resist) same (trench or via))		

50	151	(damascene and barrier and electrode) and	USPAT	2003/11/20
		(Ir or Ru or ruthenium or iridium)		15:34
-	3946	semiconductor and barrier and via and	USPAT	2003/11/20
		trench		09:49
_	1779	(semiconductor and barrier and via and	USPAT	2003/11/19
		trench) and (Ta or tantalum)	1002332	15:24
-	1439	((semiconductor and barrier and via and	USPAT	2003/11/19
	1	trench) and (Ta or tantalum)) and (polish	001111	15:23
		or polishing or cmp or polished or		13.23
	}	planarize or planarizing)		
_	461	(((semiconductor and barrier and via and	USPAT	2003/11/19
		trench) and (Ta or tantalum)) and (polish	001111	15:23
	1 1	or polishing or cmp or polished or		13.23
		planarize or planarizing)) and capacitor		
-	344	((((semiconductor and barrier and via and	USPAT	2003/11/19
		trench) and (Ta or tantalum)) and (polish	VD2111	15:24
		or polishing or cmp or polished or		10.24
		planarize or planarizing)) and capacitor)		
		and (copper or Cu)		
~	187	(((((semiconductor and barrier and via	USPAT	2003/11/19
		and trench) and (Ta or tantalum)) and	001111	15:25
	}	(polish or polishing or cmp or polished		13.23
		or planarize or planarizing)) and		
		capacitor) and (copper or Cu)) and ((Ta		
	1	or tantalum) with barrier)		ĺ
<del></del>	172	(((((semiconductor and barrier and via	USPAT	2003/11/19
	1	and trench) and (Ta or tantalum)) and	001111	15:25
		(polish or polishing or cmp or polished		13.23
		or planarize or planarizing)) and		
	[	capacitor) and (copper or Cu)) and ((Ta		
		or tantalum) with barrier)) and @ay<=2001		